



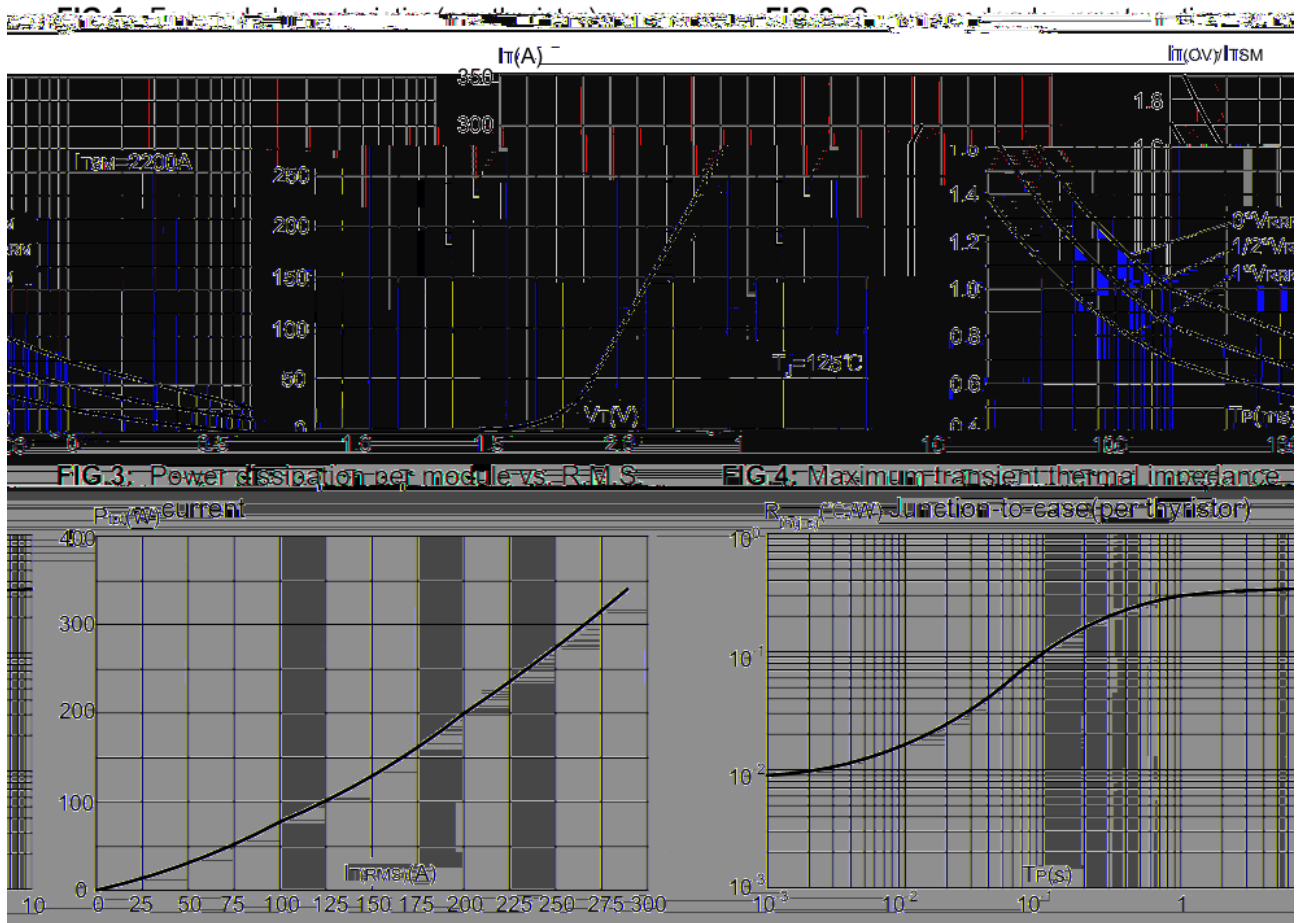
(@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

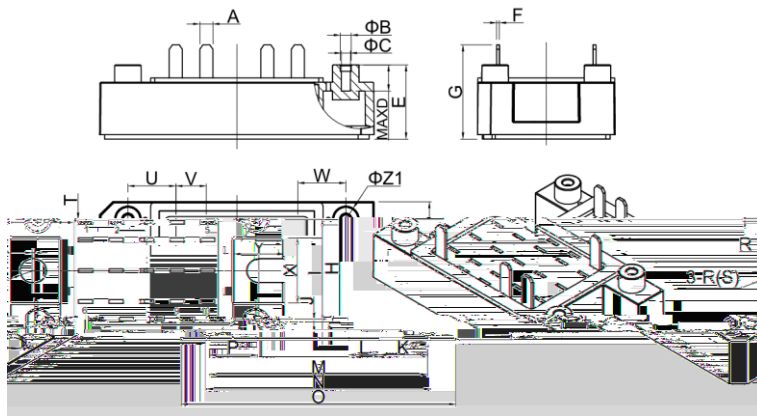
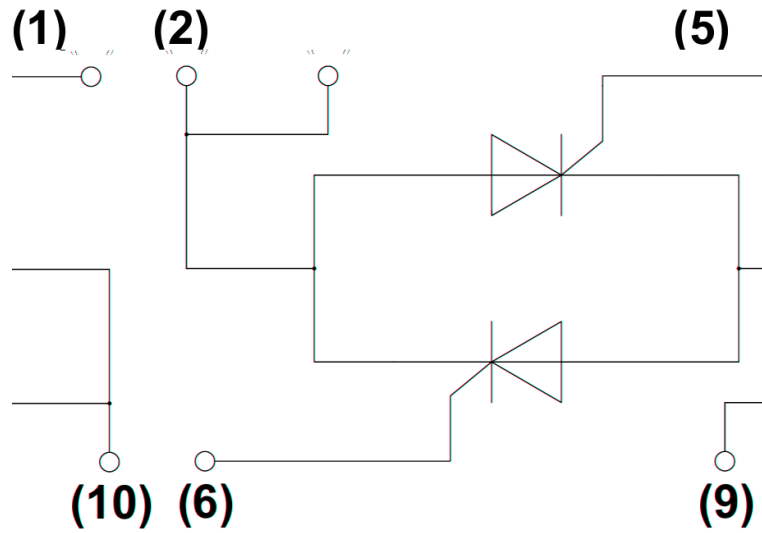
Peak forward voltage	$I_T=300\text{A}$, $t_P=380\mu\text{s}$	V_T			1.80	V
Repetitive peak off-state current	$V_D = V_{\text{DRM}}$, $T_{vj} = 25^\circ\text{C}$	I_{DRM}			100	μA
	$V_D = V_{\text{DRM}}$, $T_{vj} = 125^\circ\text{C}$				30	mA
Reverse leakage current	$V_R = V_{\text{RRM}}$, $T_{vj} = 25^\circ\text{C}$	I_{RRM}			100	μA
	$V_R = V_{\text{RRM}}$, $T_{vj} = 125^\circ\text{C}$				30	mA
Threshold voltage	For power loss calculation only $T_{vj} = 125^\circ\text{C}$,	V_{TO}			0.9	V
Dynamic resistance	$T_{vj} = 125^\circ\text{C}$,	r_T			2.1	$\text{m}\Omega$
Triggering gate current	$V_D=12\text{V}$ $R_L=30\Omega$	I_{GT}	20		120	mA
Holding current	$I_T=1\text{A}$	I_H			250	mA
Latching current	$I_G=1.2 I_{\text{GT}}$	I_L			300	mA
Critical rate of rise of voltage	$V_D=2/3V_{\text{DRM}}$ $T_{vj}=125^\circ\text{C}$ Gate Open	dv/dt	1000			$\text{V}/\mu\text{s}$
Triggering gate voltage	$V_D=12\text{V}$ $R_L=30\Omega$	V_{GT}			1.8	V
Non triggering gate voltage	$V_D=V_{\text{DRM}}$ $T_{vj}=125^\circ\text{C}$	V_{GD}	0.25			V

(@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Thermal resistance, junction to case	per Thyristor	$R_{\text{th(j-c)}}$		0.35		/W
Mounting torque	Module torque to heatsink	M	1.7		2.3	N m

JMT150KQ18V1C	JMT150KQ18V1C	V1	42.9g/PCS	60 PCS	360 PCS





Unit of measurement: mm

Ref	Dimensions					
	Millimeters			Inches		
6	17.75	0.640	0.669	0.699	0.026	0.030
25	17.75	0.640	0.669	0.699	0.026	0.030
55	0.65	0.022	0.026	0.030	0.008	0.010
85	21.6	0.821	0.850	0.880	0.032	0.035
105	23.35	0.821	0.850	0.880	0.032	0.035
125	23.35	0.821	0.850	0.880	0.032	0.035
145	23.35	0.821	0.850	0.880	0.032	0.035
165	23.35	0.821	0.850	0.880	0.032	0.035
185	23.35	0.821	0.850	0.880	0.032	0.035
205	23.35	0.821	0.850	0.880	0.032	0.035
225	23.35	0.821	0.850	0.880	0.032	0.035
245	23.35	0.821	0.850	0.880	0.032	0.035
265	23.35	0.821	0.850	0.880	0.032	0.035
285	23.35	0.821	0.850	0.880	0.032	0.035
305	23.35	0.821	0.850	0.880	0.032	0.035
325	23.35	0.821	0.850	0.880	0.032	0.035
345	23.35	0.821	0.850	0.880	0.032	0.035
365	23.35	0.821	0.850	0.880	0.032	0.035
385	23.35	0.821	0.850	0.880	0.032	0.035
405	23.35	0.821	0.850	0.880	0.032	0.035
425	23.35	0.821	0.850	0.880	0.032	0.035
445	23.35	0.821	0.850	0.880	0.032	0.035
465	23.35	0.821	0.850	0.880	0.032	0.035
485	23.35	0.821	0.850	0.880	0.032	0.035
505	23.35	0.821	0.850	0.880	0.032	0.035
525	23.35	0.821	0.850	0.880	0.032	0.035
545	23.35	0.821	0.850	0.880	0.032	0.035
565	23.35	0.821	0.850	0.880	0.032	0.035
585	23.35	0.821	0.850	0.880	0.032	0.035
605	23.35	0.821	0.850	0.880	0.032	0.035
625	23.35	0.821	0.850	0.880	0.032	0.035
645	23.35	0.821	0.850	0.880	0.032	0.035
665	23.35	0.821	0.850	0.880	0.032	0.035
685	23.35	0.821	0.850	0.880	0.032	0.035
705	23.35	0.821	0.850	0.880	0.032	0.035
725	23.35	0.821	0.850	0.880	0.032	0.035
745	23.35	0.821	0.850	0.880	0.032	0.035
765	23.35	0.821	0.850	0.880	0.032	0.035
785	23.35	0.821	0.850	0.880	0.032	0.035
805	23.35	0.821	0.850	0.880	0.032	0.035
825	23.35	0.821	0.850	0.880	0.032	0.035
845	23.35	0.821	0.850	0.880	0.032	0.035
865	23.35	0.821	0.850	0.880	0.032	0.035
885	23.35	0.821	0.850	0.880	0.032	0.035
905	23.35	0.821	0.850	0.880	0.032	0.035
925	23.35	0.821	0.850	0.880	0.032	0.035
945	23.35	0.821	0.850	0.880	0.032	0.035
965	23.35	0.821	0.850	0.880	0.032	0.035
985	23.35	0.821	0.850	0.880	0.032	0.035
1005	23.35	0.821	0.850	0.880	0.032	0.035



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